L Number	Hits	Search Text	DB	Time stamp
-	92	(257/168).CCLS.	USPAT; US-PGPUB;	2002/02/05
_	312	(257/173).CCLS.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/05 20:15
	9	(("257/168").CCLS.) and (("257/173").CCLS.)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/05 20:15
_	4	plurality adj2 bipolar adj transistor.clm. and esd	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/05 20:16
_	36	((("257/168").CCLS.) or (("257/173").CCLS.)) and esd and bipolar adj transistor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:17
-	40	(plurality adj2 bipolar adj transistor.clm. and esd) or (((("257/168").CCLS.) or (("257/173").CCLS.)) and esd and bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:22
-	547		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:23
_	117	resistor and esd and ((parallel or lateral\$2) near3 bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05
_	152	charpentier.in.	EPO_	2002/02/05 20:35
	395	(("257/173").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/07
	166	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:43
_	97	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:47
-	94	-	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:48

				1
-	94	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12	USPAT; US-PGPUB; EPO; JPO;	2002/02/06 08:51
		protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12	DERWENT; IBM_TDB	
		transistor) and (parallel near12 (transistor or connect\$3 or load))	_	
-	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or	USPAT; US-PGPUB;	2002/02/06 08:51
		electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12	EPO; JPO; DERWENT; IBM_TDB	•
		transistor) and (parallel near12 (transistor or connect\$3 or load))and		
_	93	bipolar.ti,ab. (("257/168").CCLS.) or	USPAT;	2002/02/06
		(("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar	US-PGPUB; EPO; JPO; DERWENT;	08:52
		adj transistor) and (plurality near12 transistor) and (parallel near12	IBM_TDB	
		<pre>(transistor or connect\$3 or load))and bipolar.ti,ab. and (ic or integrated adj circuit)</pre>		
-	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or	USPAT; US-PGPUB;	2002/02/06 08:54
		electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar	EPO; JPO; DERWENT;	
		adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load))and	IBM_TDB	
	•	bipolar.ti,ab. and (ic or integrated adj circuit) and bus		2002/02/06
	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12	USPAT; US-PGPUB; EPO; JPO;	2002/02/06 08:54
		protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12	DERWENT; IBM_TDB	
		transistor) and (parallel near12 (transistor or connect\$3 or load)) and bipolar.ti,ab. and (ic or integrated adj		
-	31	circuit) and bus ((("257/168").CCLS.) or	USPAT;	2002/02/06
		(("257/173").CCLS.)) and esd adj protect\$3.ti,ab.	US-PGPUB; EPO; JPO; DERWENT;	08:57
_	20	(((("257/168").CCLS.) or	IBM_TDB USPAT;	2002/02/06
		(("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2 transistor	US-PGPUB; EPO; JPO; DERWENT;	08:57
-	16	((((("257/168").CCLS.) or	IBM_TDB USPAT;	2002/02/06
		(("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2 transistor) and resist\$3	US-PGPUB; EPO; JPO; DERWENT;	09:14
-	3	5043782.pn.	IBM_TDB USPAT;	2002/02/06
			US-PGPUB; EPO; JPO; DERWENT;	09:16
_	2	5708550.pn.	IBM_TDB USPAT;	2002/02/06
		-	US-PGPUB; EPO; JPO;	09:15
			DERWENT; IBM_TDB	

	r·			10000/00/00
_	2	jp-61292351\$-\$.did.	USPAT; US-PGPUB;	2002/02/06 09:16
			EPO; JPO; DERWENT;	
_	395	((257/168) or (257/173)).CCLS.	IBM_TDB USPAT;	2002/02/06
		((20,),100, 01 (20,),100220	US-PGPUB;	11:37
			EPO; JPO;	
			DERWENT; IBM TDB	
-	0	("L3 and esd adj2 protection.ti,ab.").PN.	USPĀT;	2002/02/06
			US-PGPUB; EPO; JPO;	10:58
			DERWENT;	
		(100-100-100-100-100-100-100-100-100-100	IBM_TDB	0000 (00 (00
-	29	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab.	USPAT; US-PGPUB;	2002/02/06
		esa aajz protection.cr,ab.	EPO; JPO;	10.00
			DERWENT;	
	7	((("257/168") or ("257/173")).CCLS.) and	IBM_TDB USPAT;	2002/02/06
	'	esd adj2 protection.ti,ab. and	US-PGPUB;	10:59
		bipolar.ti,ab.	EPO; JPO;	
			DERWENT; IBM TDB	
_	0	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06
		esd adj2 protection.ti,ab. and	US-PGPUB;	10:59
		bipolar.ti,ab. and plurality adj2 bipolar	EPO; JPO; DERWENT;	
			IBM_TDB	
-	0	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and	USPAT; US-PGPUB;	2002/02/06 11:00
		bipolar.ti,ab. and plurality adj2	EPO; JPO;	
		transistor	DERWENT;	
_	15	((("257/168") or ("257/173")).CCLS.) and	<pre>IBM_TDB USPAT;</pre>	2002/02/06
		esd adj2 protection.ti,ab. and bipolar	US-PGPUB;	11:00
		adj transistor	EPO; JPO; DERWENT;	
			IBM TDB	
_	12	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06
		esd adj2 protection.ti,ab. and bipolar adj transistor and resist\$3	US-PGPUB; EPO; JPO;	11:02
		and organization with representation	DERWENT;	
	_	///#257/160#\ om /#257/172#\\ core \	IBM_TDB	2002/02/06
-	5	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar	USPAT; US-PGPUB;	2002/02/06 11:02
		adj transistor and resist\$3 and parallel	EPO; JPO;	
:	1		DERWENT; IBM TDB	
_	3	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06
		esd adj protection.ti,ab. and bipolar adj	US-PGPUB;	11:48
		transistor.ti,ab.	EPO; JPO; DERWENT;	
			IBM_TDB	
-	131	esd adj protection.ti,ab. and bipolar adj	USPAT;	2002/02/06 11:49
		transistor.ti,ab.	US-PGPUB; EPO; JPO;	1 1 1 1 1 2 1 1 1 1 1 1 1 1 1 1 1 1 1 1
			DERWENT;	
	1	esd adj protection.ti,ab. and bipolar adj	IBM_TDB USPAT;	2002/02/06
_		transistor.ti,ab. and plurality adj2	US-PGPUB;	14:06
		(bipolar or transistor) and resist\$3 and	EPO; JPO;	
		parallel	DERWENT; IBM TDB	
_	12	esd adj protection.ti,ab. and ((advantage	USPAT;	2002/02/06 '
		or purpose) near10 \$3bipolar adj	US-PGPUB;	14:08
		transistor)	EPO; JPO; DERWENT;	,
			IBM_TDB	
· · · · · · · · · · · · · · · · · · ·	•		<del>-</del>	-

=	1	("0708550").PN.	USPAT; US-PGPUB;	2002/02/06 15:07
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	2	("5708550").PN.	USPAT;	2002/02/06
			US-PGPUB;	15:35
İ			EPO; JPO; DERWENT;	
			IBM TDB	
-	7		USPAT	2002/02/06
		("6268639") or ("5329143") or ("6172404")		15:20
	5	or ("5623387") or ("5272371")).PN. ((("5043782") or ("5708550") or	USPAT;	2002/02/06
-	]	("6268639") or ("5329143") or ("6172404")	US-PGPUB;	15:21
		or ("5623387") or ("5272371")).PN.) and	EPO; JPO;	
		(base adj region and bipolar adj	DERWENT;	
		transistor)	IBM_TDB	2002/02/06
-	0	("esd adj protection.ti,ab and bipolar adj transistor.ti,ab. and path").PN.	USPAT; US-PGPUB;	2002/02/06 15:35
		aaj stansissoi.ci,as. ana patn j.in.	EPO; JPO;	-3.00
			DERWENT;	
	_		IBM_TDB	2002/02/26
-	0	("esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and path").PN.	USPAT; US-PGPUB;	2002/02/06 15:36
		adj clansiscol.cl, ab. and pach /.rw.	EPO; JPO;	13.30
			DERWENT;	
			IBM_TDB	0000 (00 (00
-	48	esd adj protection.ti,ab. and bipolar adj	USPAT;	2002/02/06
		transistor.ti,ab. and path	US-PGPUB; EPO; JPO;	12:30
			DERWENT;	
			IBM_TDB	
-	17	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/02/06
		transistor.ti,ab. and current adj path	US-PGPUB; EPO; JPO;	15:40
			DERWENT;	
			IBM_TDB	
_	15		USPAT;	2002/02/06
		protection and (increase near12 path)	US-PGPUB; EPO; JPO;	16:49
			DERWENT;	
			IBM_TDB	
_	12		USPAT;	2002/02/06
		<pre>protection and ((base near10 (surround\$3 or enclos\$3)) near10 (emitter or</pre>	US-PGPUB; EPO; JPO;	17:01
		collector))	DERWENT;	
			IBM_TDB	
-	710	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06
		near10 (surround\$3 or enclos\$3)) near10 (emitter or collector))	US-PGPUB; EPO; JPO;	17:04
	1	(CMICCEI OF COTTECCOT)	DERWENT;	
	1		IBM_TDB	
-	506	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06
		near5 (surround\$3 or enclos\$3)) near5 (emitter or collector))	US-PGPUB; EPO; JPO;	17:05
		(emrerer or corrector))	DERWENT;	
			IBM_TDB	
-	334	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06
		near3 (surround\$3 or enclos\$3)) near3	US-PGPUB;	17:05
		(emitter or collector))	EPO; JPO; DERWENT;	
			IBM TDB	
_	2	1	USPĀT;	2002/02/06
		near3 (surround\$3 or enclos\$3)) near3	US-PGPUB;	17:07
	1	<pre>(emitter or collector)) and esd.ti,ab. and protection.ti,ab.</pre>	EPO; JPO; DERWENT;	•
		and procedition. cr, an.	IBM TDB	

	-			
	5	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06
		near4 (surround\$3 or enclos\$3)) near4	US-PGPUB;	17:10
		(emitter or collector)) and	EPO; JPO;	
		(electrostatic adj discharge or	DERWENT;	
		esd).ti,ab. and protection.ti,ab.	IBM_TDB	
-	430	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06
		near4 (surround\$3 or enclos\$3)) near4	US-PGPUB;	17:11
	1	(emitter or collector))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06
		near4 (surround\$3 or enclos\$3)) near4	US-PGPUB;	17:32
	1	(emitter or collector)) and (esd with	EPO; JPO;	
	1	protection)	DERWENT;	
			IBM_TDB	
-	997	(257/355).CCLS.	USPAT;	2002/02/06
-			US-PGPUB;	17:33
			EPO; JPO;	
			DERWENT;	
	0.5	//#057/255#\\ ggtg \\11-	IBM_TDB	2002/02/06
-	95		USPAT;	2002/02/06
]		protection and bipolar adj transistor	US-PGPUB;	17:42
			EPO; JPO;	
į			DERWENT;	
		(//#257/255#) COTC \ -=44	IBM_TDB	2002/02/06
-	4	((("257/355").CCLS.) and esd adj protection and bipolar adj transistor)	USPAT; US-PGPUB;	17:39
			EPO; JPO;	17:39
		and ((base near7 (surround\$3 or enclos\$3)) near7 (emitter or collector))		
		enclos\$3)) hear/ (emitter or collector))	DERWENT;	1
	1115	((257/360) or (257/361) or (257/362) or	USPAT;	2002/02/06
-	1113	((257/360) Of (257/361) Of (257/362) Of (257/363)).CCLS.	US-PGPUB;	17:38
		(257/363)).ССБЗ.	EPO; JPO;	17.36
	1		DERWENT;	
			IBM TDB	
_	122	((("257/360") or ("257/361") or	USPAT;	2002/02/06
_	122	("257/362") or ("257/363")).CCLS.) and	US-PGPUB;	17:39
		esd adj protection and bipolar adj	EPO; JPO;	1 1,.35
		transistor	DERWENT;	
		STAILD ID I	IBM TDB	
_	6	(((("257/360") or ("257/361") or	USPAT;	2002/02/06
		("257/362") or ("257/363")).CCLS.) and	US-PGPUB;	17:42
		esd adj protection and bipolar adj	EPO; JPO;	
		transistor) and ((base near7 (surround\$3	DERWENT;	
	1	or enclos\$3)) near7 (emitter or	IBM TDB	
		collector))	_	1
-	893	((257/370) or (257/373)).CCLS.	USPAT;	2002/02/06
			US-PGPUB;	17:41
			EPO; JPO;	
1			DERWENT;	]
			IBM_TDB	
-	7	<b>, , , , , , , , , , , , , , , , , , ,</b>	USPAT;	2002/02/06
		esd adj protection and bipolar adj	US-PGPUB;	17:42
		transistor	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(((("257/370") or ("257/373")).CCLS.) and	USPAT;	2002/02/06
		esd adj protection and bipolar adj	US-PGPUB;	18:25
		transistor) and ((base near7 (surround\$3	EPO; JPO;	
-		or enclos\$3)) near7 (emitter or	DERWENT;	
1		collector))	IBM_TDB	
-	192	, . ,	USPAT;	2002/02/06
		adj2 well	US-PGPUB;	18:28
1	1		EPO; JPO;	
1			DERWENT;	
			IBM_TDB	, ,
-	65	1 1	USPAT;	2002/02/06
		adj2 well	US-PGPUB;	18:42
			EPO; JPO;	•
			DERWENT;	
	1		IBM_TDB	

-	2	lateral adj bipolar adj transistor.ti.	USPAT;	2002/02/06
		and second adj2 well	US-PGPUB;	18:45
İ		•	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	1 45	latinal and binalon and two made to ab	USPAT;	2002/02/06
_	15			
		and second adj2 well	US-PGPUB;	18:45
	1		EPO; JPO;	
	+		DERWENT;	
			IBM_TDB	
1_	0	(source or drain) adj regions same	USPĀT;	2002/02/07
		through-contact\$3	US-PGPUB;	08:33
		tinough contactys	EPO; JPO;	00.33
	1		1	
			DERWENT;	
1			IBM_TDB	
-	3	formed adj2 "same substrate" same	USPAT;	2002/02/07
		plurality adj2 bipolar adj transistor	US-PGPUB;	10:01
	ŀ		EPO; JPO;	
			DERWENT;	
ŀ	Ì		IBM TDB	
!		//UEC22207U) /UEQ/2702U)		2002/02/07
-	4	(("5623387") or ("5043782") or	USPAT	2002/02/07
1	[	("6075271") or ("6277689")).PN.		10:02
-	0	jp-0361292351\$-\$.did.	USPAT;	2002/02/07
	1		US-PGPUB;	10:04
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
	0	2012022E16 6 444	USPAT;	2002/02/07
-	"	jp-361292351\$-\$.did.		
			US-PGPUB;	10:04
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	jp-61292351\$-\$.did.	USPAT;	2002/02/07
	_	JP 018380014 4.0140.	US-PGPUB;	10:04
			EPO; JPO;	10.01
			DERWENT;	
			IBM_TDB	
<del>-</del>	3321	((257/168) or (257/173) or (257/355) or	USPAT;	2002/11/05
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	19:14
1		(257/363) or (257/370) or	EPO; JPO;	
	1	(257/373)).CCLS.	DERWENT;	
1		, · · · · · · · · · · · · · · · · · ·	IBM TDB	
<u> </u>	119	(((257/168) or (257/173) or (257/355) or	USPAT;	2002/11/05
-	119	(((237/100) OI (237/173) OI (237/333) OI	1	
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	19:15
	1	(257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (uniformly or	DERWENT;	
	}	evenly or uniform or even) near12	IBM_TDB	
i	1	(distribution or distributed)	_	
l <b>-</b>	60	(((257/168) or (257/173) or (257/355) or	USPAT;	2002/11/05
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	19:19
	1		EPO; JPO;	
	1	(257/363) or (257/370) or	1	
	1	(257/373)).CCLS.) and (uniformly or	DERWENT;	
1		evenly or uniform or even) near12	IBM_TDB	
	1	(distribution or distributed) and (esd or		
1		electrostatic adj discharge)		
-	44	(((257/168) or (257/173) or (257/355) or	USPAT;	2002/11/05
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	19:22
		(257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (uniformly or	DERWENT;	
		evenly or uniform or even) near12	IBM_TDB	
		(distribution or distributed) and (esd or		
	-	electrostatic adj discharge) and		
		(resistor or resistance) near15		
		(transistor or fet or mis or mos or		
		mosfet or misfet or igfet or jfet or dmos		
	1			
1	1	or dmosfet or cmos or cmosfet)		l

			T	
-	45	(US-5565698-\$ or US-5742083-\$ or	USPAT;	2003/06/02
		US-5329143-\$ or US-5708550-\$ or	US-PGPUB;	08:00
		US-4724471-\$ or US-5043782-\$ or	JPO;	
		US-5281841-\$ or US-5272371-\$ or	DERWENT	1
		US-5623387-\$ or US-5701024-\$ or		
		US-5689133-\$ or US-5637900-\$ or		
		US-6229182-\$ or US-5440162-\$ or		İ
		US-5248892-\$ or US-6002156-\$ or		
1		US-6277689-\$ or US-6075271-\$ or		
j		US-6236086-\$ or US-5955763-\$ or		
		US-6172404-\$ or US-6268639-\$ or		
		US-5623156-\$ or US-6300649-\$ or		
		US-6306695-\$ or US-6388292-\$).did. or		
		(US-6441438-\$ or US-6441437-\$ or		
		US-5763919-\$ or US-6388851-\$ or		
		US-4139935-\$ or US-4763184-\$ or		
		US-6097066-\$ or US-4806999-\$ or		1
		US-5426323-\$ or US-6445039-\$ or		1
		US-4736271-\$ or US-5237395-\$ or		
		US-5939756-\$ or US-5982600-\$ or	į	
		US-6078068-\$).did. or (US-20020003236-\$	İ	
		or US-20020014665-\$).did. or		
		(JP-61292351-\$).did. or	İ	
		(JP-61292351-\$).did.	ļ	
	1	((US-5565698-\$ or US-5742083-\$ or	USPAT;	2003/06/02
_	1	US-5329143-\$ or US-5708550-\$ or	US-PGPUB;	08:10
		US-4724471-\$ or US-5043782-\$ or	JPO;	00.10
		US-5281841-\$ or US-5272371-\$ or	DERWENT	
		US-5623387-\$ or US-5701024-\$ or	DEKWENT	
		US-5689133-\$ or US-5637900-\$ or	İ	
		US-6229182-\$ or US-5440162-\$ or		
		US-5248892-\$ or US-6002156-\$ or		
		US-6277689-\$ or US-6075271-\$ or	İ	
		US-6236086-\$ or US-5955763-\$ or		
		US-6172404-\$ or US-6268639-\$ or		
		,	İ	
		US-5623156-\$ or US-6300649-\$ or		
		US-6306695-\$ or US-6388292-\$).did. or		
		(US-6441438-\$ or US-6441437-\$ or		
		US-5763919-\$ or US-6388851-\$ or		
		US-4139935-\$ or US-4763184-\$ or		
		US-6097066-\$ or US-4806999-\$ or		
		US-5426323-\$ or US-6445039-\$ or		
		US-4736271-\$ or US-5237395-\$ or	Ì	
		US-5939756-\$ or US-5982600-\$ or		
		US-6078068-\$).did. or (US-20020003236-\$		
		or US-20020014665-\$).did. or		
		(JP-61292351-\$).did. or		
		(JP-61292351-\$).did.) and wada.in.	<u> </u>	<u> </u>

-	2	((US-5565698-\$ or US-5742083-\$ or	USPAT;	2003/06/02
		US-5329143-\$ or US-5708550-\$ or	US-PGPUB;	08:29
		US-4724471-\$ or US-5043782-\$ or	JPO;	
		US-5281841-\$ or US-5272371-\$ or	DERWENT	
		US-5623387-\$ or US-5701024-\$ or		
		US-5689133-\$ or US-5637900-\$ or		
		US-6229182-\$ or US-5440162-\$ or	İ	1
		US-5248892-\$ or US-6002156-\$ or		
		US-6277689-\$ or US-6075271-\$ or		
		US-6236086-\$ or US-5955763-\$ or		
		US-6172404-\$ or US-6268639-\$ or		
		US-5623156-\$ or US-6300649-\$ or		
		US-6306695-\$ or US-6388292-\$).did. or		
		(US-6441438-\$ or US-6441437-\$ or		į.
		US-5763919-\$ or US-6388851-\$ or		
		US-4139935-\$ or US-4763184-\$ or		
		US-6097066-\$ or US-4806999-\$ or		
		US-5426323-\$ or US-6445039-\$ or		
		US-4736271-\$ or US-5237395-\$ or		
		US-5939756-\$ or US-5982600-\$ or		
1		US-6078068-\$).did. or (US-20020003236-\$		
		or US-20020014665-\$).did. or		
		(JP-61292351-\$).did. or		
ļ		(JP-61292351-\$).did.) and avery.in.		
_	o	1 · · · · · · · · · · · · · · · · · · ·	USPAT;	2003/06/02
			US-PGPUB;	08:30
			JPO;	
			DERWENT	
_	9	transistor adj array and control nearl	USPAT;	2003/06/02
		(connexion connection)	US-PGPUB;	08:33
		(Connexion Connection)	JPO;	*****
			DERWENT	
_	7	transistor adj array and shunt adj	USPAT;	2003/06/02
	·	resistor	US-PGPUB;	08:36
		16313661	JPO;	****
			DERWENT	
_	1	shunt adj resistor near4 (separate each	USPAT;	2003/06/02
	-	every) and (257/\$6.ccls. 438/\$6.ccls.)	US-PGPUB;	08:38
		every, and \23// \0.0015. 130/ \0.0015./	EPO; JPO;	*************************************
			DERWENT;	
			IBM TDB	l
_	21	shunt adj resistor near4 (separate each	USPAT;	2003/06/02
	21	every)	US-PGPUB;	08:40
		CVCLY	EPO; JPO;	00.10
			DERWENT;	ļ
			IBM TDB	
1_	0	shunt adj resistor near4 (separate each	USPAT;	2003/06/02
		every) and transistor and array	US-PGPUB;	08:41
		diality and desired and array	EPO; JPO;	
1			DERWENT;	
	·		IBM_TDB	
_	266	resistor near4 (separate each every) and	USPAT;	2003/06/02
	200	transistor and array	US-PGPUB;	08:52
		orange of and array	EPO; JPO;	
			DERWENT;	]
			IBM_TDB	į i
_	7	   (bipolar adj transistor igbt) near2 array	USPAT;	2003/06/02
	l '	and base near3 resistor	US-PGPUB;	08:58
		and base hears resistor	EPO; JPO;	55.55
		· ·	DERWENT;	
			IBM TDB	]
_	16	shunt adj resistance and bipolar adj	USPAT;	2003/06/02
_	10	transistor and array	US-PGPUB;	09:06
	[	cransiscor and array	EPO; JPO;	05.00
1			DERWENT;	
				.
I _	3290	((257/168) or (257/173) or (257/355) or	IBM_TDB USPAT;	2003/06/02
	3290	((257/166) or (257/173) or (257/363) or (257/360) or (257/361) or (257/362) or	US-PGPUB;	09:07
		(257/360) of (257/361) of (257/362) of (257/370) or (257/373)).CCLS.	EPO; JPO;	05.07
	1	(231/310) OF (231/313)).CCE3.	DERWENT;	
1	l	L	IBM_TDB	l

_	12		USPAT;	2003/06/02
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	09:09
		(257/370) or (257/373)).CCLS.) and	EPO; JPO;	
		bipolar adj transistor near5 array and	DERWENT;	
		resistor	IBM_TDB	
-	6		USPAT;	2003/06/02
		resistor and (esd electrostatic adj	US-PGPUB;	09:16
		discharge)	EPO; JPO;	]
			DERWENT;	
			IBM_TDB	İ
<b>-</b>	2	("6472286").PN.	USPAT;	2003/06/02
			US-PGPUB;	12:11
			EPO; JPO;	İ
			DERWENT;	!
			IBM_TDB	
-	1	"6008524".PN.	USPAT	2003/06/02
				09:17
-	1	"5850095".PN.	USPAT	2003/06/02
				09:23
_	3484	((257/168) or (257/173) or (257/355) or	USPAT;	2003/06/07
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	17:38
		(257/362) or (257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.	DERWENT;	
			IBM TDB	
_	641	(((257/168) or (257/173) or (257/355) or	USPAT;	2003/06/07
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	17:40
		(257/362) or (257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (electrostatic adj	DERWENT;	
		discharge esd).ti,ab,clm.	IBM_TDB	
_	17	(((257/168) or (257/173) or (257/355) or	USPAT;	2003/06/07
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	17:45
		(257/362) or (257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (electrostatic adj	DERWENT;	j l
		discharge esd).ti,ab,clm. and protect\$3	IBM_TDB	
		near12 parallel near12 (resistor	_	1
		resistance)		1
-	0	(electrostatic adj discharge	USPAT;	2003/06/07
		esd).ti,ab,clm. and protect\$3 near12	US-PGPUB;	17:46
		parallel near12 track near2 (resistor	EPO; JPO;	
		resistance)	DERWENT;	
			IBM_TDB	
-	76	(electrostatic adj discharge	USPAT;	2003/06/07
		esd).ti,ab,clm. and protect\$3 near12	US-PGPUB;	17:48
		parallel near12 (resistor resistance)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
<del>-</del>	58	(electrostatic adj discharge	USPAT;	2003/06/07
		esd).ti,ab,clm. and protect\$3 near12	US-PGPUB;	18:42
		parallel near12 (resistor resistance) and	EPO; JPO;	
		transistor	DERWENT;	
]			IBM_TDB	/
-	2	("5043782").PN.	USPAT;	2003/06/07
			US-PGPUB;	19:01
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("6075271").PN.	USPAT;	2003/06/07
			US-PGPUB;	19:02
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	